

| Notice of Allowability | Application No. | Applicant(s) | |
|---|--|--|---------------------------|
| | 10/761,658 Examiner | SHIN ET AL. | |
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| | PHUC T. DANG | 2818 | |
| The MAILING DATE of this communication apperation allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313 | (OR REMAINS) CLOSED in this app or other appropriate communication IGHTS. This application is subject to | olication. If not include will be mailed in due | ed course. THIS |
| 1. \boxtimes This communication is responsive to <u>amendment filed July</u> | <u> 26, 2005</u> . | | |
| 2. The allowed claim(s) is/are <u>1-20</u> . | | | |
| 3. \boxtimes The drawings filed on <u>20 January 2004</u> are accepted by the | e Examiner. | | |
| 4. Acknowledgment is made of a claim for foreign priority ur a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do | e been received. e been received in Application No | | tion from the |
| International Bureau (PCT Rule 17.2(a)). | cuments have been received in this | national stage applica | tion from the |
| * Certified copies not received: | | | 4 n |
| Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subminformal patent application (PTO-152) which give | IENT of this application. itted. Note the attached EXAMINER | 'S AMENDMENT or N | |
| | | | |
| CORRECTED DRAWINGS (as "replacement sheets") mus (a) ☐ including changes required by the Notice of Draftspers | | .048) attached | |
| (a) ☐ including changes required by the Notice of Branspers 1) ☐ hereto or 2) ☐ to Paper No./Mail Date | - | o 40) attached | |
| (b) ☐ including changes required by the attached Examiner's Paper No./Mail Date | | Office action of | |
| Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t | .84(c)) should be written on the drawir he header according to 37 CFR 1.121(| ngs in the front (not the d). | back) of |
| 7. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT | sit of BIOLOGICAL MATERIAL r FOR THE DEPOSIT OF BIOLOGIC | nust be submitted. I AL MATERIAL | Note the |
| | | | |
| Attachment(s) | | | 0.450) |
| 1. Notice of References Cited (PTO-892) | 5. Notice of Informal P | • | O-152) |
| 2. Notice of Draftperson's Patent Drawing Review (PTO-948) | 6. ☐ Interview Summary Paper No./Mail Da | | |
| 3. Information Disclosure Statements (PTO-1449 or PTO/SB/C Paper No./Mail Date | | | |
| 4. Examiner's Comment Regarding Requirement for Deposit | 8. 🛛 Examiner's Stateme | ent of Reasons for Alic | owance |
| of Biological Material | 9. | | |
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| PH | UC T. DANG | Langshur | |
| PRI | MARY EXAMINER | N | |

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DETAILED ACTION

1. Claims 1-20 are allowed.

2. The following is an examiner's statement of reasons for allowance:

None of the prior art teaches an apparatus and a method of operating a CMOS semiconductor product, comprising the step of <u>forming a metal oxide semiconductor transistor</u> of the second polarity formed upon the first doped well and a metal oxide semiconductor transistor of the first polarity formed upon the second doped well after forming a third doped well of the second polarity laterally and vertically surrounding the first doped well of the first polarity in combination with the other structures found in the independent apparatus claim 1 and with the steps found in the independent method claim 11.

None of the prior art teaches an apparatus and a method of operating a CMOS semiconductor product, comprising the step of <u>forming a p metal oxide semiconductor transistor</u> upon the <u>first n doped well and a p metal oxide semiconductor transistor formed upon the first n doped well after forming a second n doped well laterally and vertically surrounding the p doped well in combination with the other structures found in the independent apparatus claim 6 and with the steps found in the independent method claim 16.</u>

3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submission should be clearly labeled "Comments on Statement of Reasons for Allowance".

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4. Any inquiry concerning this communication or earlier communications from the examiner

should be directed to Phuc T. Dang whose telephone number is (571) 272-1776. The examiner

can normally be reached on 8:00 am-5:00 pm.

5. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor,

David C. Nelms can be reached on (571) 272-1787. The fax phone numbers for the organization

where this application or proceeding is assigned are 571-273-8300 for regular communications

and After Final communications.

6. Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is 703-308-0956.

Langohur

Phuc T. Dang

Primary Examiner

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